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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



NJT4030P, NJV4030P

Bipolar Power Transistors

PNP Silicon

Features

- Epoxy Meets UL 94, V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CB}	40	Vdc
Emitter-Base Voltage	V_{EB}	6.0	Vdc
Base Current - Continuous	I_B	1.0	Adc
Collector Current - Continuous	I_C	3.0	Adc
Collector Current - Peak	I_{CM}	5.0	Adc
ESD - Human Body Model	HBM	3B	V
ESD - Machine Model	MM	C	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Power Dissipation Total P_D @ $T_A = 25^\circ\text{C}$ (Note 1) Total P_D @ $T_A = 25^\circ\text{C}$ (Note 2)	P_D	2.0 0.80	W
Thermal Resistance, Junction-to-Case Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	$R_{\theta JA}$ $R_{\theta JA}$	64 155	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T_L	260	$^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

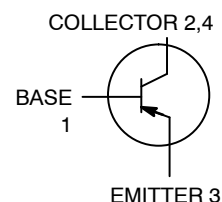
1. Mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material.
2. Mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material.



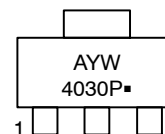
ON Semiconductor®

<http://onsemi.com>

PNP TRANSISTOR
3.0 AMPERES
40 VOLTS, 2.0 WATTS



MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- W = Work Week
- 4030P = Specific Device Code
- = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NJT4030PT1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
NJV4030PT1G		
NJT4030PT3G	SOT-223 (Pb-Free)	4000 / Tape & Reel
NJV4030PT3G		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NJT4030P, NJV4030P

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (I _C = 10 mA _{dc} , I _B = 0 A _{dc})	V _{CEO(sus)}	40	–	–	V _{dc}
Emitter–Base Voltage (I _E = 50 μA _{dc} , I _C = 0 A _{dc})	V _{EBO}	6.0	–	–	V _{dc}
Collector Cutoff Current (V _{CB} = 40 V _{dc})	I _{CBO}	–	–	100	nA _{dc}
Emitter Cutoff Current (V _{BE} = 6.0 V _{dc})	I _{EBO}	–	–	100	nA _{dc}

ON CHARACTERISTICS (Note 3)

Collector–Emitter Saturation Voltage (I _C = 0.5 A _{dc} , I _B = 5.0 mA _{dc}) (I _C = 1.0 A _{dc} , I _B = 10 mA _{dc}) (I _C = 3.0 A _{dc} , I _B = 0.3 A _{dc})	V _{CE(sat)}	–	–	0.150 0.200 0.500	V _{dc}
Base–Emitter Saturation Voltage (I _C = 1.0 A _{dc} , I _B = 0.1 A _{dc})	V _{BE(sat)}	–	–	1.0	V _{dc}
Base–Emitter On Voltage (I _C = 1.0 A _{dc} , V _{CE} = 2.0 V _{dc})	V _{BE(on)}	–	–	1.0	V _{dc}
DC Current Gain (I _C = 0.5 A _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 1.0 A _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 3.0 A _{dc} , V _{CE} = 1.0 V _{dc})	h _{FE}	220 200 100	– – –	– 400 –	–

DYNAMIC CHARACTERISTICS

Output Capacitance (V _{CB} = 10 V _{dc} , f = 1.0 MHz)	C _{ob}	–	40	–	pF
Input Capacitance (V _{EB} = 5.0 V _{dc} , f = 1.0 MHz)	C _{ib}	–	130	–	pF
Current–Gain – Bandwidth Product (Note 4) (I _C = 500 mA, V _{CE} = 10 V, F _{test} = 1.0 MHz)	f _T	–	160	–	MHz

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. f_T = |h_{FE}| • f_{test}

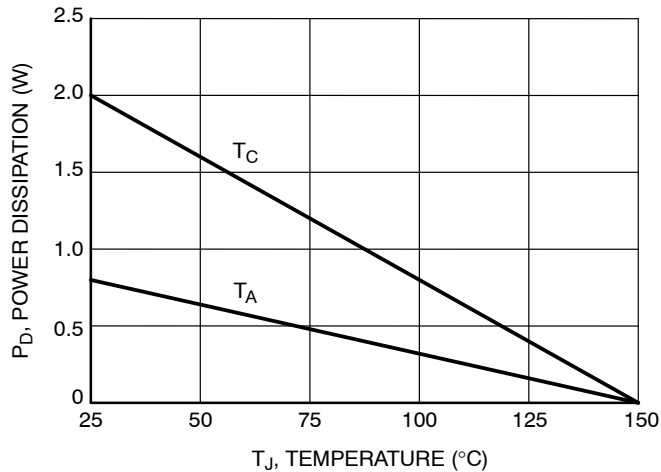


Figure 1. Power Derating

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TYPICAL CHARACTERISTICS

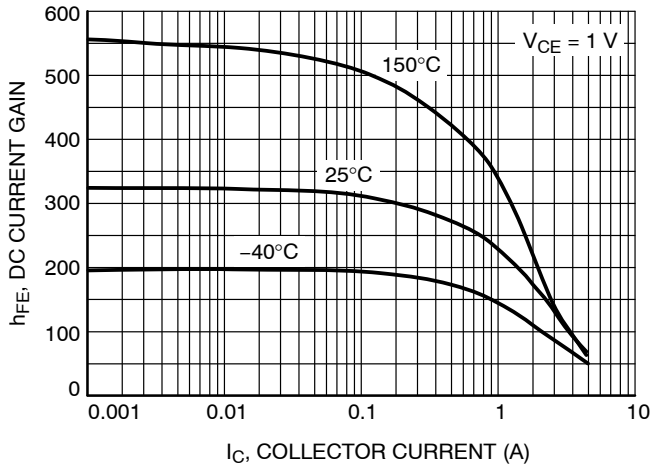


Figure 2. DC Current Gain

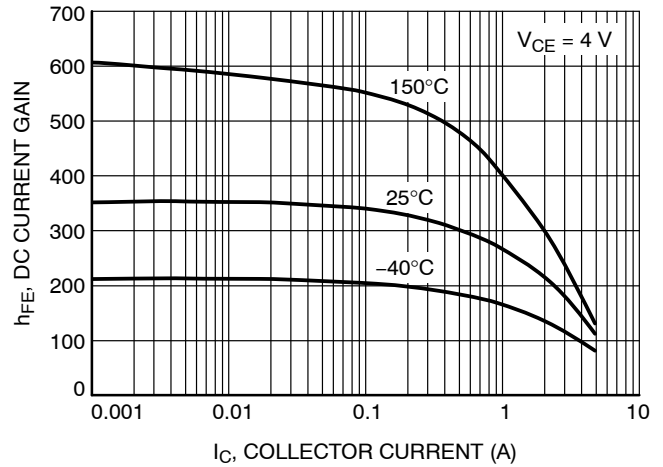


Figure 3. DC Current Gain

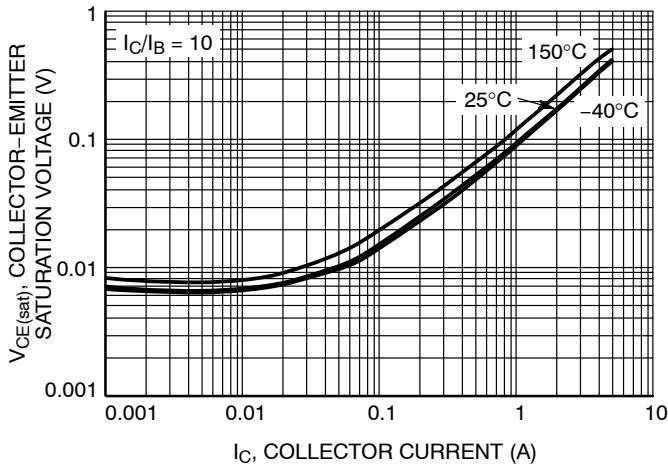


Figure 4. Collector-Emitter Saturation Voltage

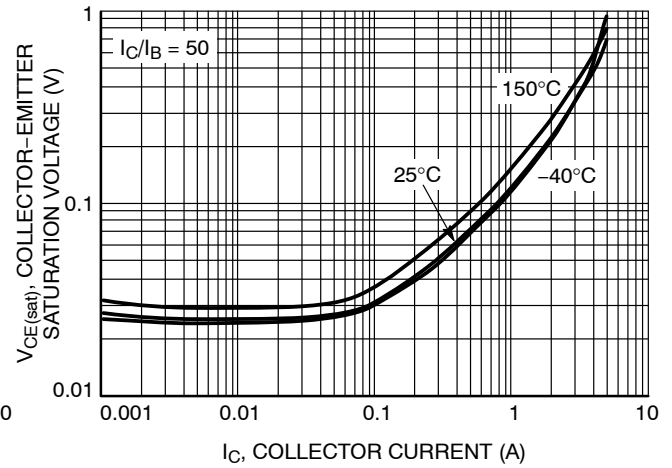


Figure 5. Collector-Emitter Saturation Voltage

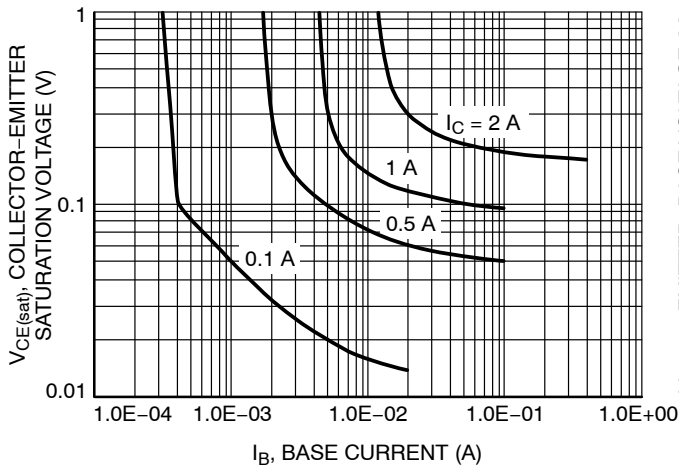


Figure 6. Collector Saturation Region

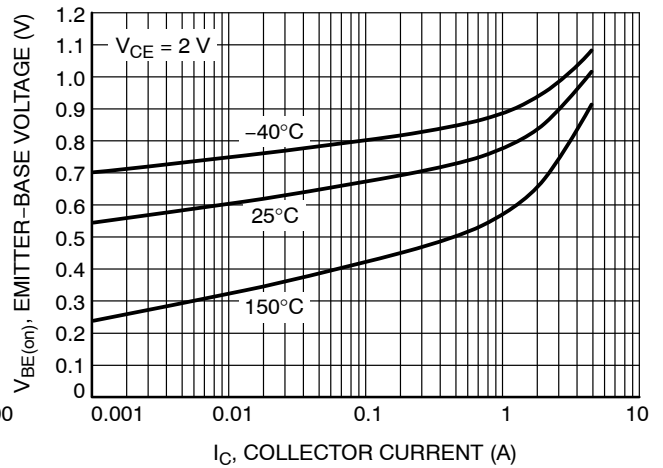


Figure 7. $V_{BE(on)}$ Voltage

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TYPICAL CHARACTERISTICS

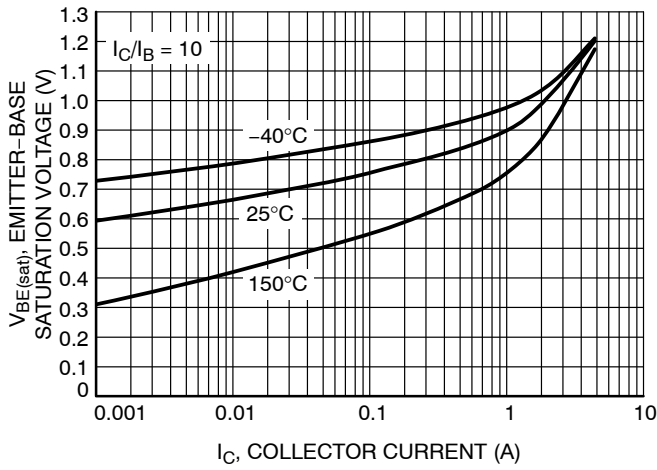


Figure 8. Base-Emitter Saturation Voltage

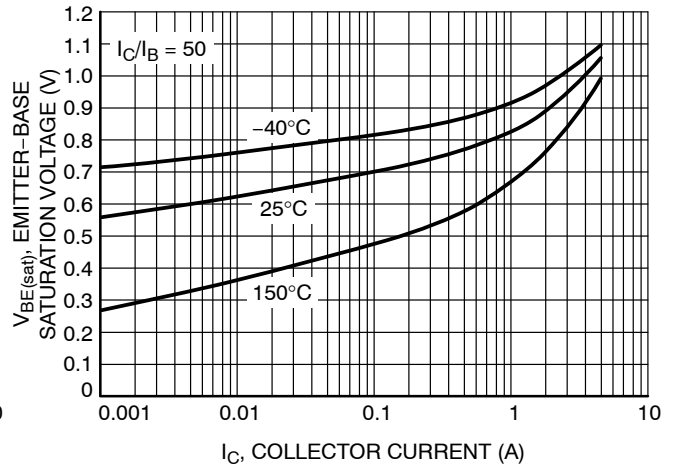


Figure 9. Base-Emitter Saturation Voltage

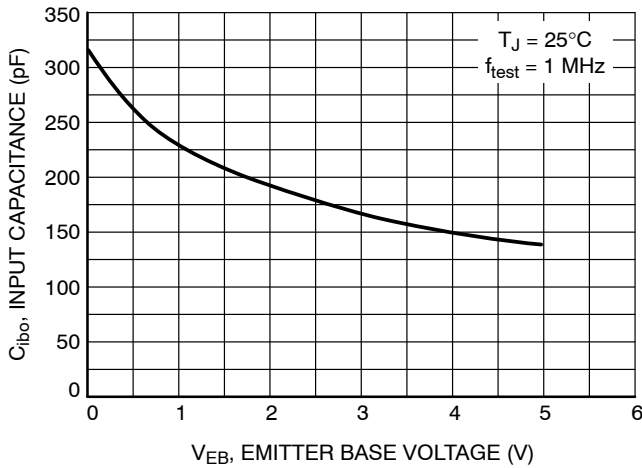


Figure 10. Input Capacitance

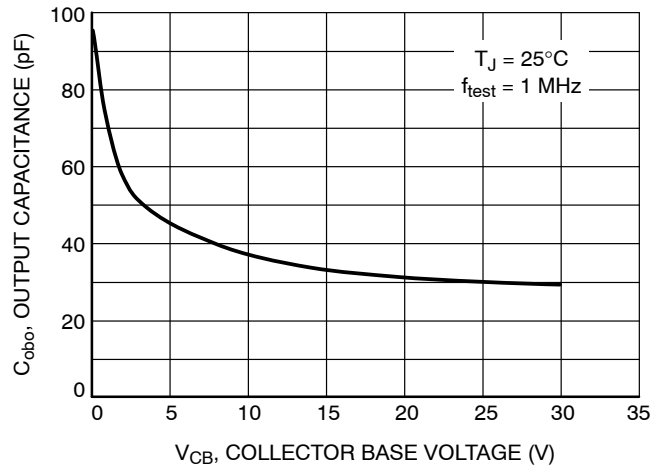


Figure 11. Output Capacitance

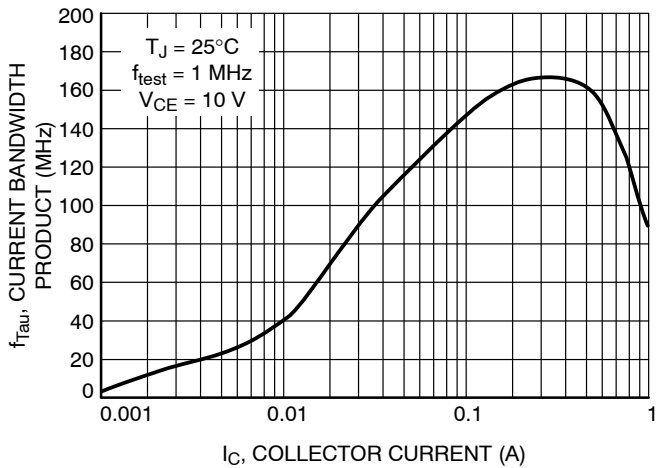


Figure 12. Current-Gain Bandwidth Product

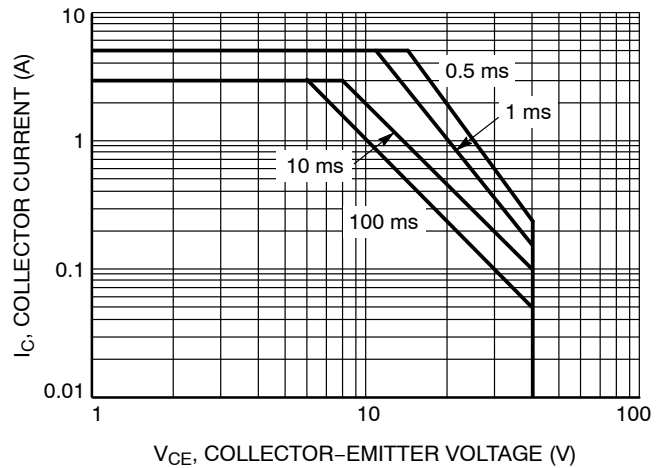
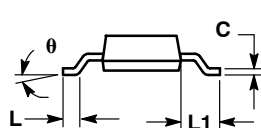
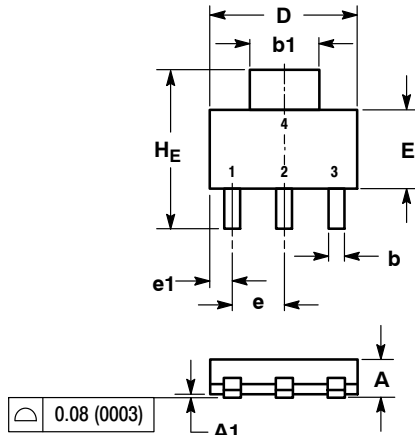


Figure 13. Safe Operating Area

NJT4030P, NJV4030P

PACKAGE DIMENSIONS

SOT-223 (TO-261)
CASE 318E-04
ISSUE N



NOTES:

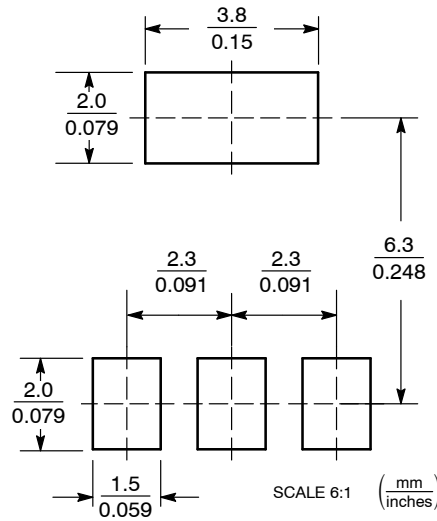
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	---	---	0.008	---	---
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°

STYLE 1:

- PIN 1. BASE
- COLLECTOR
- EMITTER
- COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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